## **BT148W series**

#### GENERAL DESCRIPTION

Glass passivated, sensitive gate thyristors in a plastic envelope suitable for surface mounting, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

#### **PINNING - SOT223**

PIN	PIN DESCRIPTION		
1	cathode		
2	anode		
3	gate		
tab	anode		

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>drm</sub> , V <sub>rrm</sub>	BT148W- Repetitive peak off-state voltages	<b>400R</b> 400	<b>500R</b> 500	<b>600R</b> 600	V
I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Average on-state current RMS on-state current Non-repetitive peak on-state current	0.6 1 10	0.6 1 10	0.6 1 10	A A A

### PIN CONFIGURATION

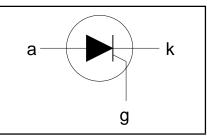
1

4

2

3

### SYMBOL



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
$V_{drm}, V_{rrm}$	Repetitive peak off-state voltages		-	<b>-400R</b> 400 <sup>1</sup>	<b>-500R</b> 500 <sup>1</sup>	<b>-600R</b> 600 <sup>1</sup>	V
I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{sp} \le 112 \degree C$ all conduction angles half sine wave; $T_j = 25 \degree C$ prior to surge	-		0.6 1		A A
		t = 10 ms t = 8.3 ms	-		10 11		A A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 10 ms	-		0.5		A <sup>2</sup> s
dl <sub>⊤</sub> /dt	Repetitive rate of rise of on-state current after triggering	I <sub>TM</sub> = 4 A; I <sub>G</sub> = 200 mA; dI <sub>G</sub> /dt = 200 mA/μs	-		50		A/μs
I <sub>GM</sub>	Peak gate current		-		1		Α
I <sub>GM</sub> V <sub>GM</sub>	Peak gate voltage		-		5		V
V <sub>RGM</sub>	Peak reverse gate voltage		-		5		V
P <sub>GM</sub>	Peak gate power	over any 20 ms period	-		1.2 0.12		W W
$\begin{array}{c} P_{G(AV)}^{\text{OM}} \\ T_{stg} \\ T_{j} \end{array}$	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		150 125 <sup>2</sup>		°° ℃

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

**<sup>2</sup>** Note: Operation above 110°C may require the use of a gate to cathode resistor of  $1k\Omega$  or less.

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-sp</sub>	Thermal resistance junction to solder point		-	-	15	K/W
R <sub>th j-a</sub>	Thermal resistance	pcb mounted, minimum footprint pcb mounted, pad area as in fig:14	-	156 70	-	K/W K/W

## STATIC CHARACTERISTICS

 $T_i = 25$  °C unless otherwise stated

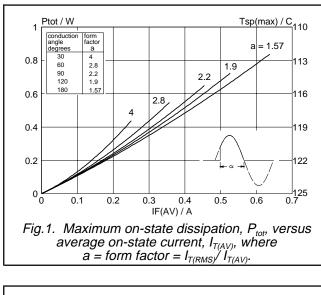
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_{\rm D} = 12 \text{ V}; \text{ I}_{\rm T} = 0.1 \text{ A}$	-	50	200	μA
	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	0.17	10	mΑ
I <sub>H</sub>	Holding current	$V_{\rm D} = 12 \text{ V}; \text{ I}_{\rm GT} = 0.1 \text{ A}$	-	0.10	6	mA
V <sub>τ</sub>	On-state voltage	$I_T = 2 A$	-	1.3	1.5	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{\rm D} = 12 \text{ V}; \text{ I}_{\rm T} = 0.1 \text{ A}$	-	0.4	1.5	V
		$V_{\rm R} = V_{\rm RRM(max)}$ ; $I_{\rm T} = 0.1$ A; $T_{\rm i} = 110$ °C	0.1	0.2	-	V
I <sub>D</sub> , I <sub>R</sub>	Off-state leakage current	$V_D = V_{DRM(max)}^{(rud)}; V_R = V_{RRM(max)}; T_j = 125 \ ^{\circ}C$	-	0.1	0.5	mA

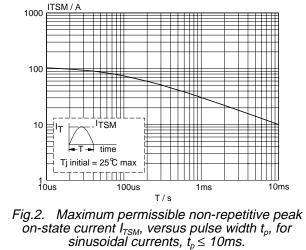
## **DYNAMIC CHARACTERISTICS**

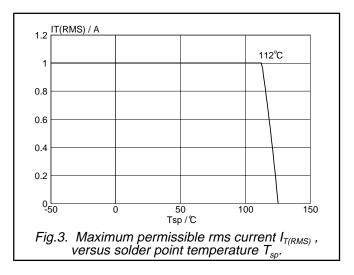
 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM}$ = 67% $V_{DRM(max)}$ ; T <sub>j</sub> = 125 °C; exponential waveform; R <sub>GK</sub> = 100 Ω	-	50	-	V/µs
t <sub>gt</sub>	Gate controlled turn-on	$I_{TM} = 4 \text{ A}; V_D = V_{DRM(max)}; I_G = 5 \text{ mA};$ $I_{DC}/dt = 0.2 \text{ A/us}$	-	2	-	μs
t <sub>q</sub>	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}; T_j = 125 °C; I_{TM} = 2 A; V_R = 35 V; dI_{TM}/dt = 30 A/\mu s; dV_D/dt = 2 V/\mu s; R_{GK} = 1 k\Omega$	-	100	-	μs

## **BT148W** series







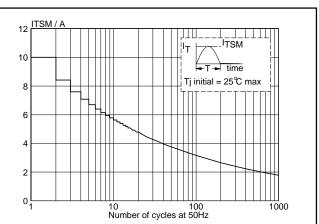
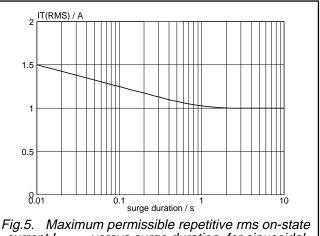
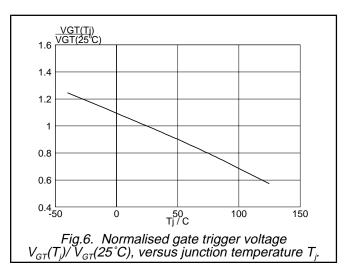


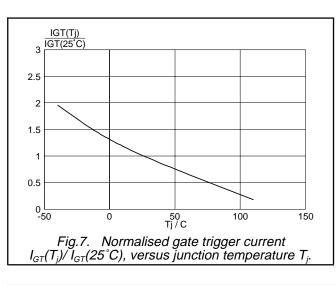
Fig.4. Maximum permissible non-repetitive peak on-state current I<sub>TSM</sub>, versus number of cycles, for sinusoidal currents, f = 50 Hz.

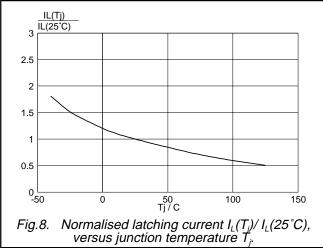


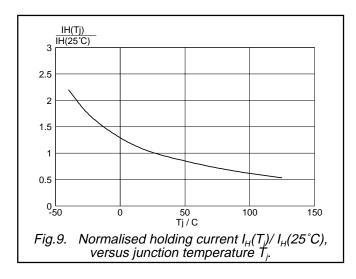
current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{sp} \le 112^{\circ}C$ .

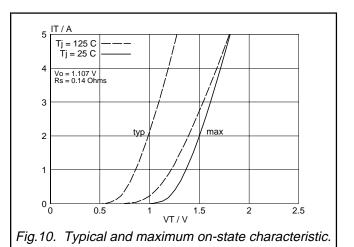


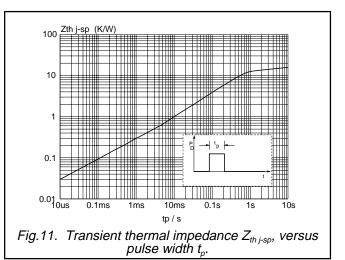
## BT148W series

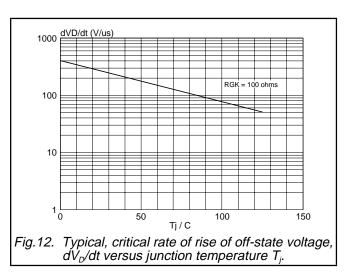








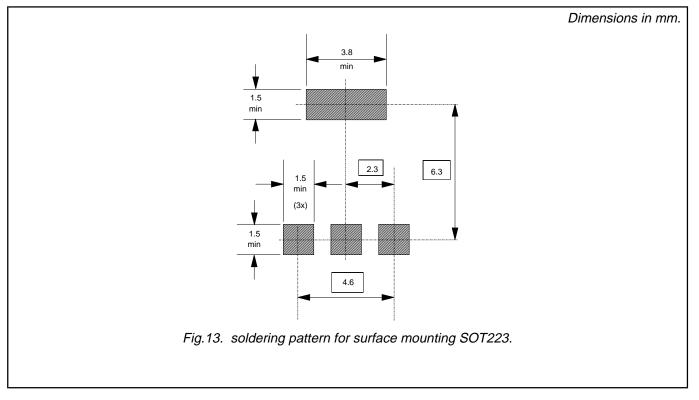




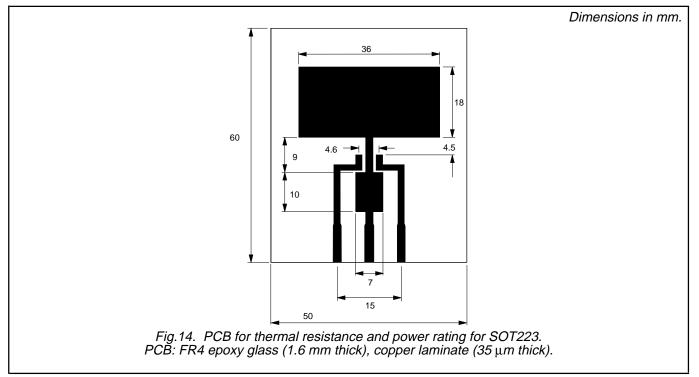
## BT148W series

Thyristors logic level

### **MOUNTING INSTRUCTIONS**

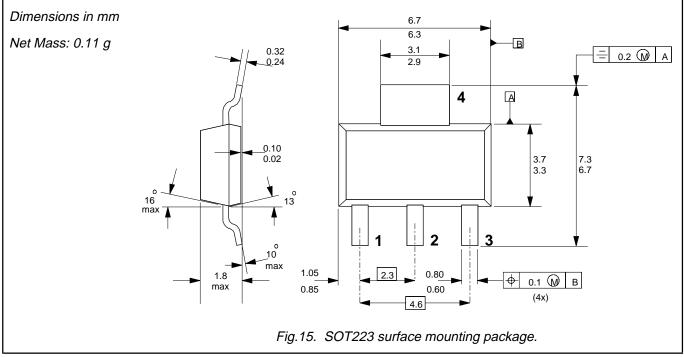


#### PRINTED CIRCUIT BOARD



## **BT148W** series

### **MECHANICAL DATA**



#### Notes

For further information, refer to Philips publication SC18 " SMD Footprint Design and Soldering Guidelines". Order code: 9397 750 00505.
Epoxy meets UL94 V0 at 1/8".

## DEFINITIONS

Data sheet status				
Objective specification	Dbjective specification This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				
Where application inform	ation is given, it is advisory and does not form part of the specification.			

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